

Amendments to the Specification:

Page 6, amend the paragraph beginning on line 22 to read as follows.

Furthermore, a process monitoring method according to the present invention comprises the steps of recording in advance a relationship between feature index of each three-dimensional pattern shape and a device property of a circuit containing patterns each having the feature index, setting a tolerance level of a three-dimensional shape of a pattern necessary to realize a desired device property, based on information about the recorded relationship, and monitoring the presence or absence of an ~~anomaly~~ abnormality of a pattern forming process, based on the calculated tolerance level and feature index of a three-dimensional shape of a pattern to be evaluated.

Page 16, amend the paragraph beginning on line 24 to read as follows.

The primary electron beam 202 emitted from the electron gun 201 converges on the condenser lens 203, and is focused on the wafer 100 placed on the stage 101 through the beam deflector 204, the ExB deflector 205 and the objective lens 206 and irradiated thereon. When the electron ~~beam~~ beam is applied thereto, a secondary electron is produced from the wafer 100.

Page 36, amend the paragraph beginning on line 5 to read as follows.

If the relationship between the pattern shape and device properties has already been obtained as shown in Fig. ~~5A~~ 15A, for example, then the relationship of these can be determined by the regression analysis.